

# MOS FET MTM862270LBF

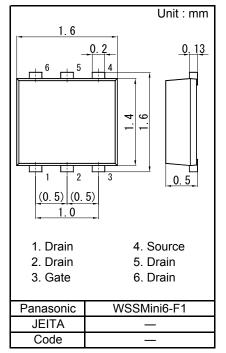
# MTM862270LBF Silicon N-channel MOSFET

#### For Switching

- Features
- Low drain-source On-state Resistance : RDS(on) typ = 80 m  $\Omega$  (VGS = 4.0 V)
- Low drive voltage:1.8V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol : JF

Packaging

Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)

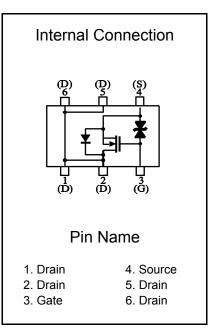


#### ■ Absolute Maximum Ratings Ta = 25 °C

| Parameter                                   | Symbol | Rating      | Unit |  |  |  |  |
|---|--------|-------------|------|--|--|--|--|
| Drain to Source Voltage                     | VDS    | 20          | V    |  |  |  |  |
| Gate to Source Voltage                      | VGS    | ±10         | v    |  |  |  |  |
| Drain Current                               | ID     | 2.2         | Δ    |  |  |  |  |
| Drain Current (Pulsed) <sup>*1</sup>        | IDp    | 8.0         | 7    |  |  |  |  |
| Total Power Dissipation <sup>*2</sup>       | PD     | 540         | mW   |  |  |  |  |
| Channel Temperature                         | Tch    | 150         |      |  |  |  |  |
| Operating Ambient Temperature               | Topr   | -40 to +85  | °C   |  |  |  |  |
| Storage Temperature Range                   | Tstg   | -55 to +150 |      |  |  |  |  |
| Noto) *1 Pulso width t < 10 us Duty cyclo < | 1 0/   |             |      |  |  |  |  |

Note) \*1 Pulse width  $t \le 10 \ \mu s$ , Duty cycle  $\le 1 \ \%$ 

\*2 Measuring on ceramic substrate at 40 mm × 38 mm × 0.2 mm PD absolute maximum rating without a heat shink: 150 mW





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■ Electrical Characteristics Ta = 25 °C ± 3 °C

| Parameter                                      | Symbol   | Conditions                     | Min | Тур  | Max | Unit |
|--|----------|--------------------------------|-----|------|-----|------|
| Drain-source Breakdown Voltage                 | VDSS     | ID = 1.0 mA, VGS = 0           | 20  |      |     | V    |
| Zero Gate Voltage Drain Current                | IDSS     | VDS = 20 V, VGS = 0            |     |      | 1.0 | μA   |
| Gate-source Leakage Current                    | IGSS     | VGS = ±8.0 V, VDS = 0          |     |      | ±10 | μA   |
| Gate-source Threshold Voltage                  | Vth      | ID = 1.0 mA, VDS = 10 V        | 0.4 | 0.85 | 1.3 | V    |
| Drain-source On-state Resistance <sup>*1</sup> | RDS(on)1 | ID = 1.0 A, VGS = 4.0 V        |     | 80   | 105 | mΩ   |
|  | RDS(on)2 | ID = 0.5 A, VGS = 2.5 V        |     | 100  | 150 | mΩ   |
|  | RDS(on)3 | ID = 0.5 A, VGS = 1.8 V        |     | 170  | 300 | mΩ   |
| Forward transfer admittance <sup>*1</sup>      | Yfs      | ID = 1.0 A, VDS = 10 V         | 3.0 | 4.0  |     | S    |
| Input Capacitance                              | Ciss     | VDS = 10 V, VGS = 0, f = 1 MHz |     | 280  |     | pF   |
| Output Capacitance                             | Coss     |                                |     | 18   |     | pF   |
| Reverse Transfer Capacitance                   | Crss     |                                |     | 17   |     | pF   |
| Turn-on time <sup>*2</sup>                     | ton      | VDD = 10 V, VGS = 0 to 4 V     | 12  |      |     | ne   |
|  |          | ID = 1.0 A                     |     | 12   |     | ns   |
| Turn-off time *2                               | toff     | VDD = 10 V, VGS = 4 to 0 V     |     | 50   |     | ns   |
|  |          | ID = 1.0 A                     | 50  | - 50 |     |      |

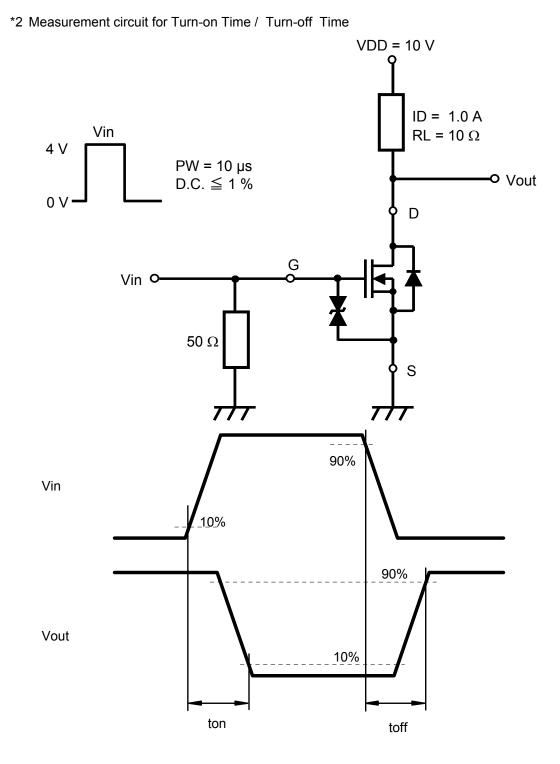
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors. 2. \*1 Pulse test

\*2 Measurement circuit for Turn-on Time / Turn-off Time

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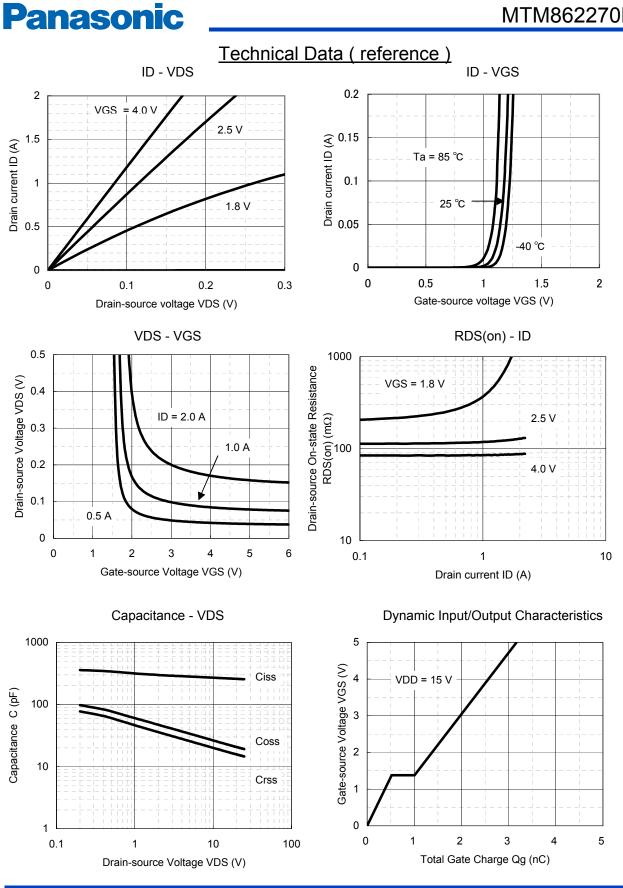


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Established : 2007-09-21 Revised : 2013-09-10

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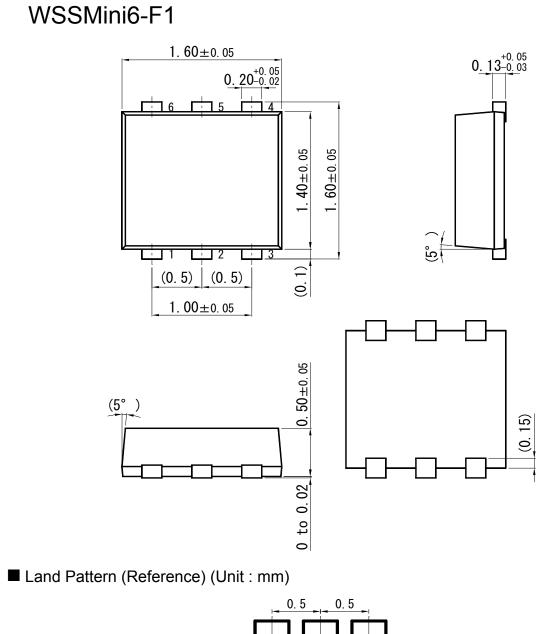


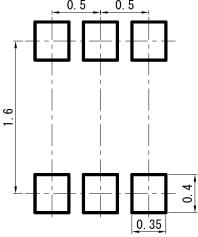
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#### MOS FET **Panasonic** MTM862270LBF Technical Data (reference) RDS(on) - Ta Vth - Ta 2 300 Gate-source Threshold voltage Drain-source On-resistance RDS(on) (mΩ) VGS = 1.8 V 250 1.5 200 Vth (V) 2.5 V 1 150 100 0.5 4.0 V 50 0 0 -50 0 50 100 150 -50 0 50 100 150 Temperature (°C) Temperature(°C) PD - Ta 1 Total Power Dissipation PD (W) 0.8 Mounted on ceramic board $(40 \times 38 \times 0.2 \text{ mm})$ 0.6 0.4 Non-heat sink 0.2 0 0 50 100 150 Temperature Ta (°C) Rth - tsw Safe Operating Area 100 1000 IDp = 8 A Thermal Resistance Rth (°C/W) 10 100 Drain Current ID (A) 1 1 ms 10 10 ms 0.1 Operation in this area 100 ms is limited by RDS(on) 1 1 s Ta = 25 °C, 0.01 Glass epoxy board (25.4 × 25.4 t0.8 mm) DC coated with copper foil, which has more than 300 mm<sup>2</sup> 0.1 0.001 0.1 0.01 1 10 100 1000 0.01 0.1 10 100 1 Drain-source Voltage VDS (V) Pulse Width tsw (s)

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#### Unit : mm

MTM862270LBF

MOS FET

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